

Yihui Wang

October 11, 2022

ECE 6240

Lab#4+5 NAND gate Schematic + Test Bench + Simulation (DC + VTC) + Layout

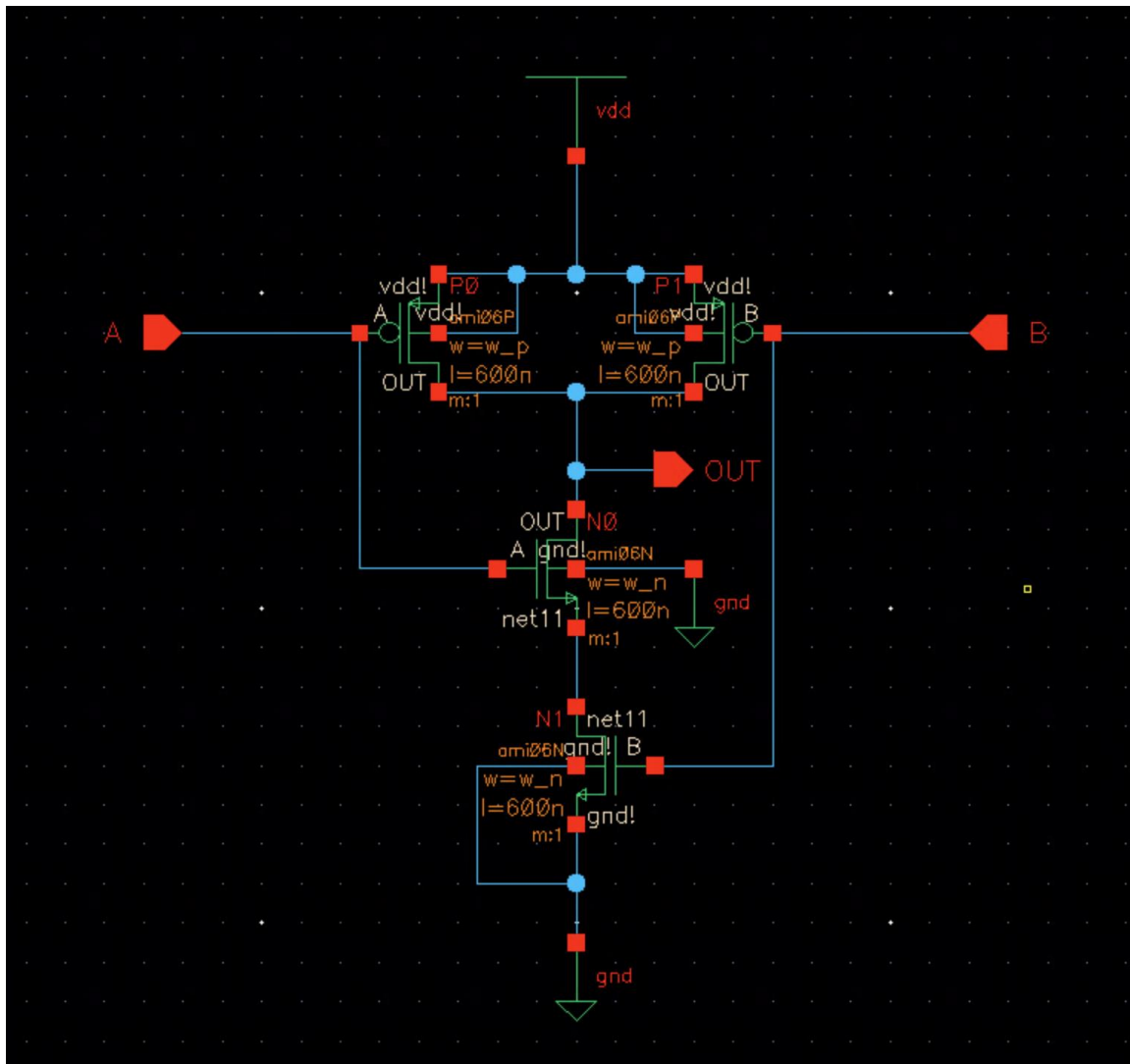


Figure 1 Schematic

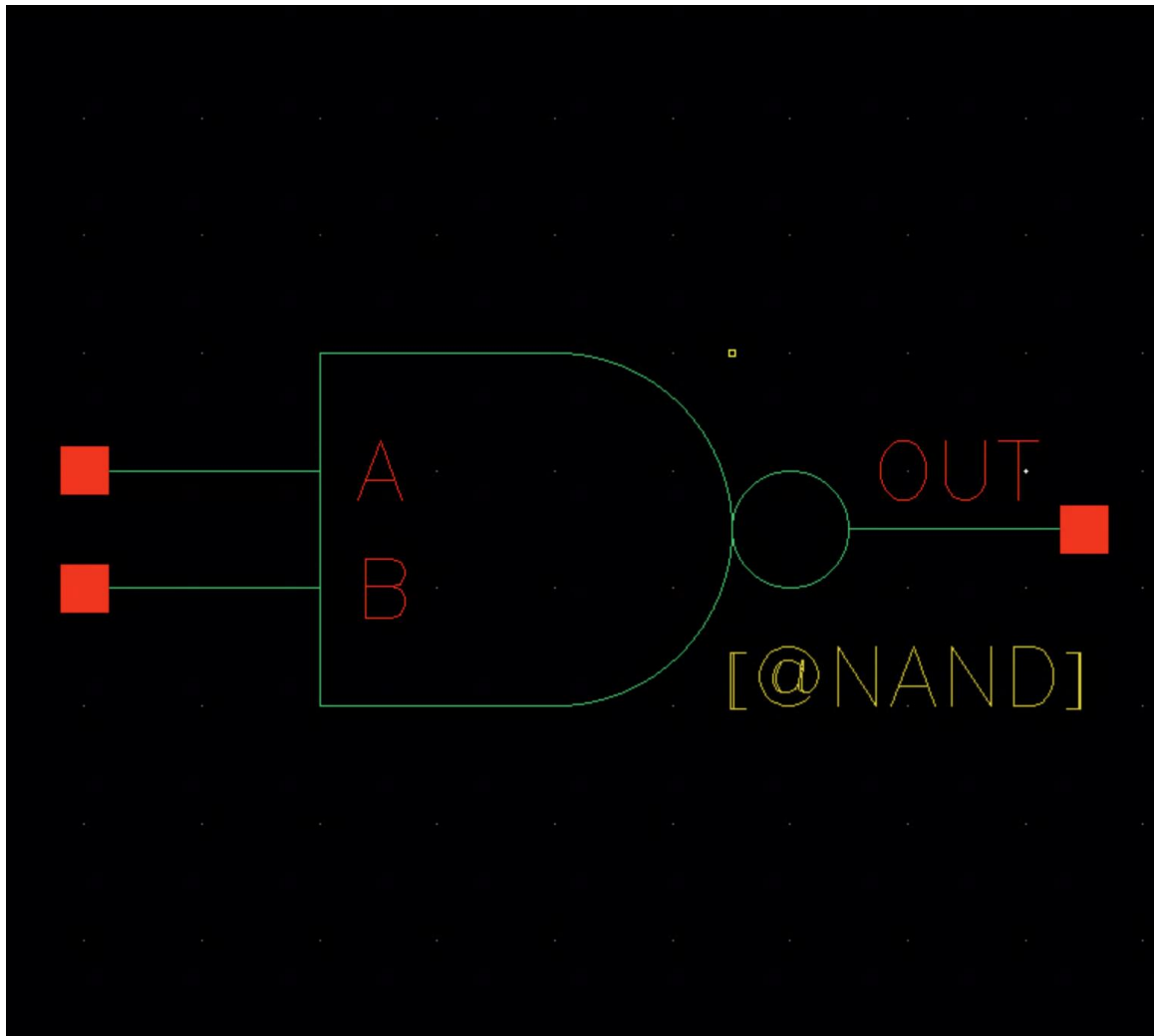


Figure 2 Symbol

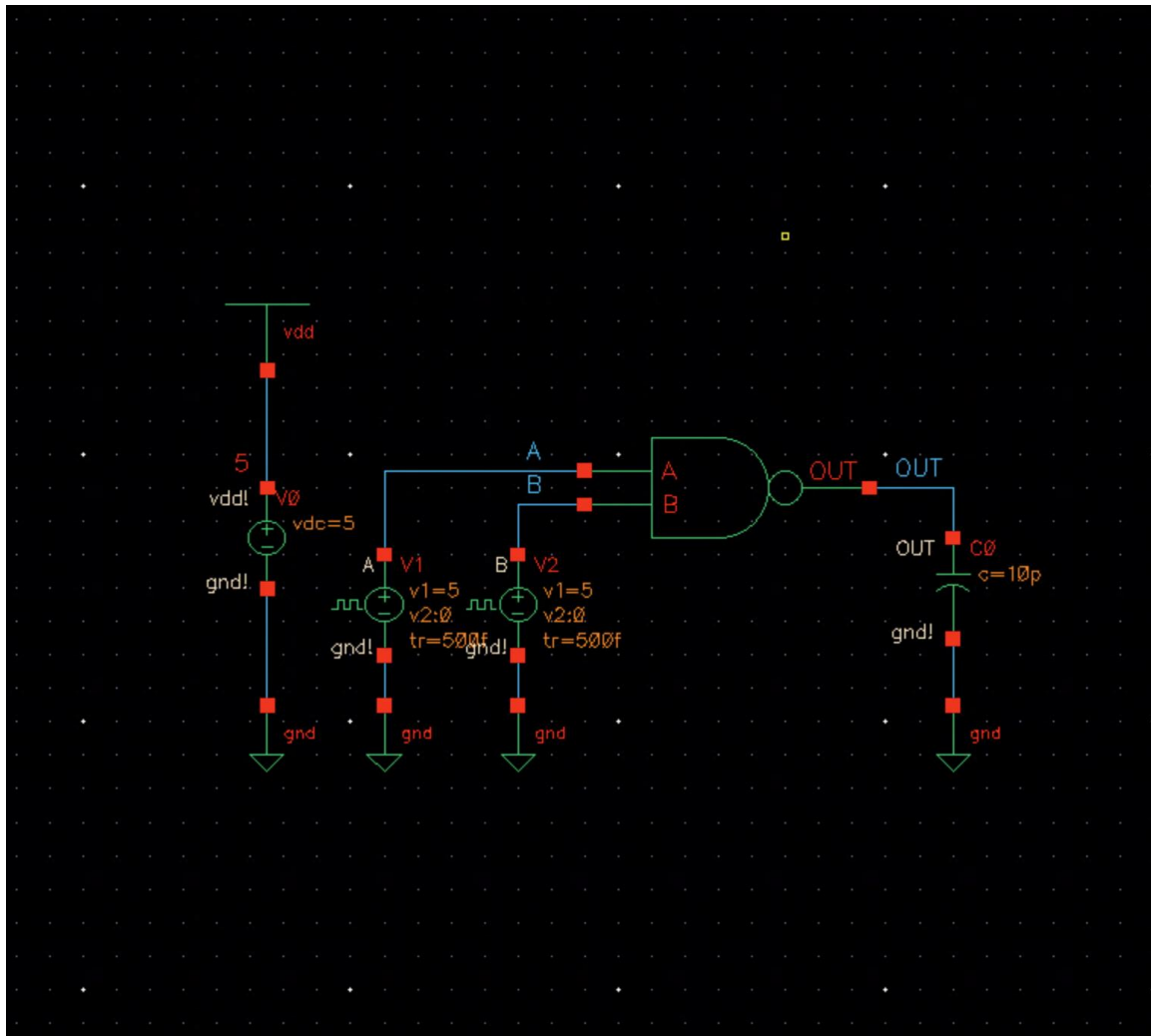


Figure 3 Testbench schematic

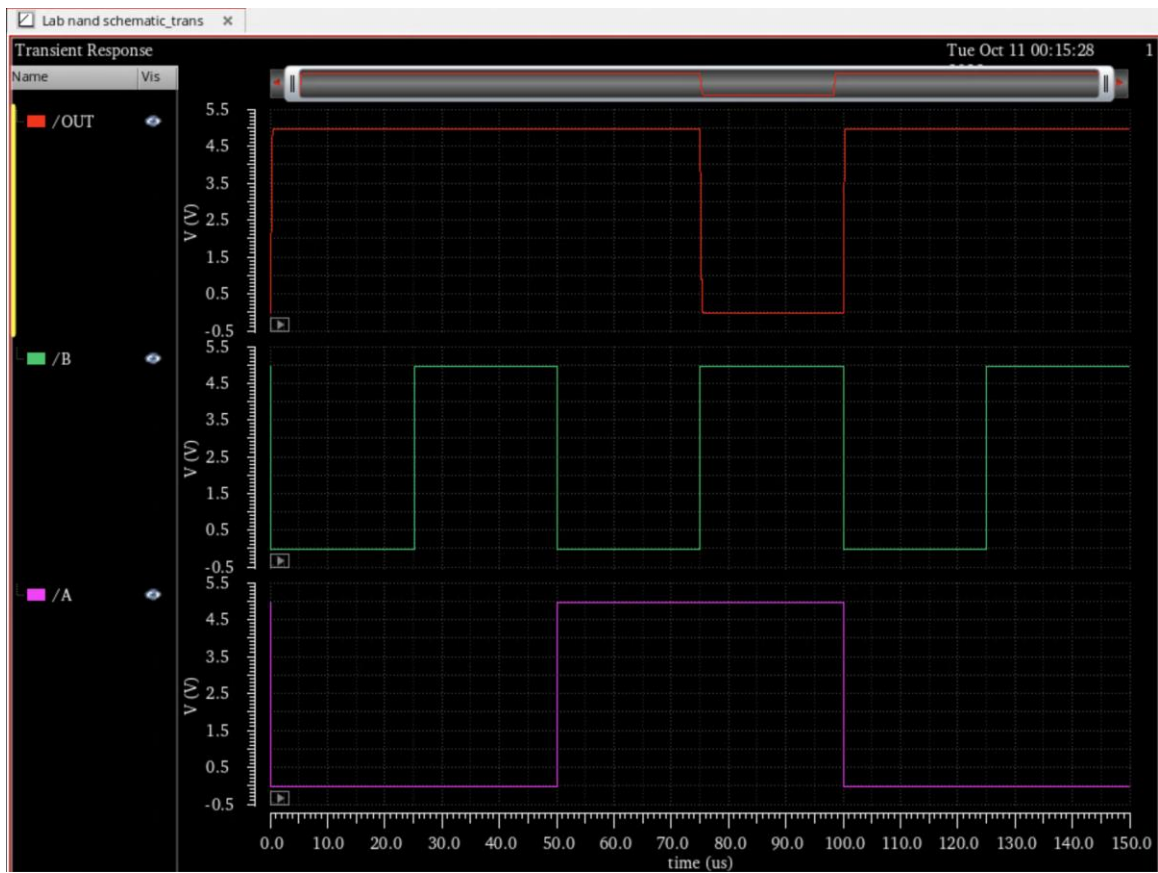


Figure 4 Transient Simulation

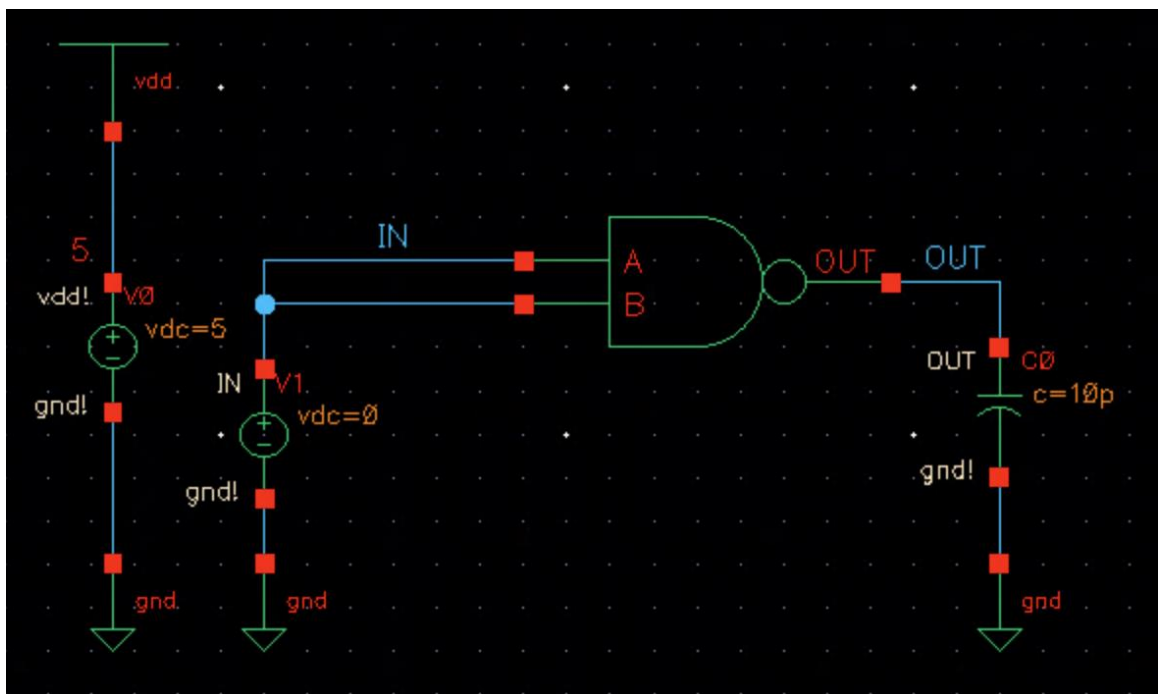


Figure 5 VTC Testbench Schematic

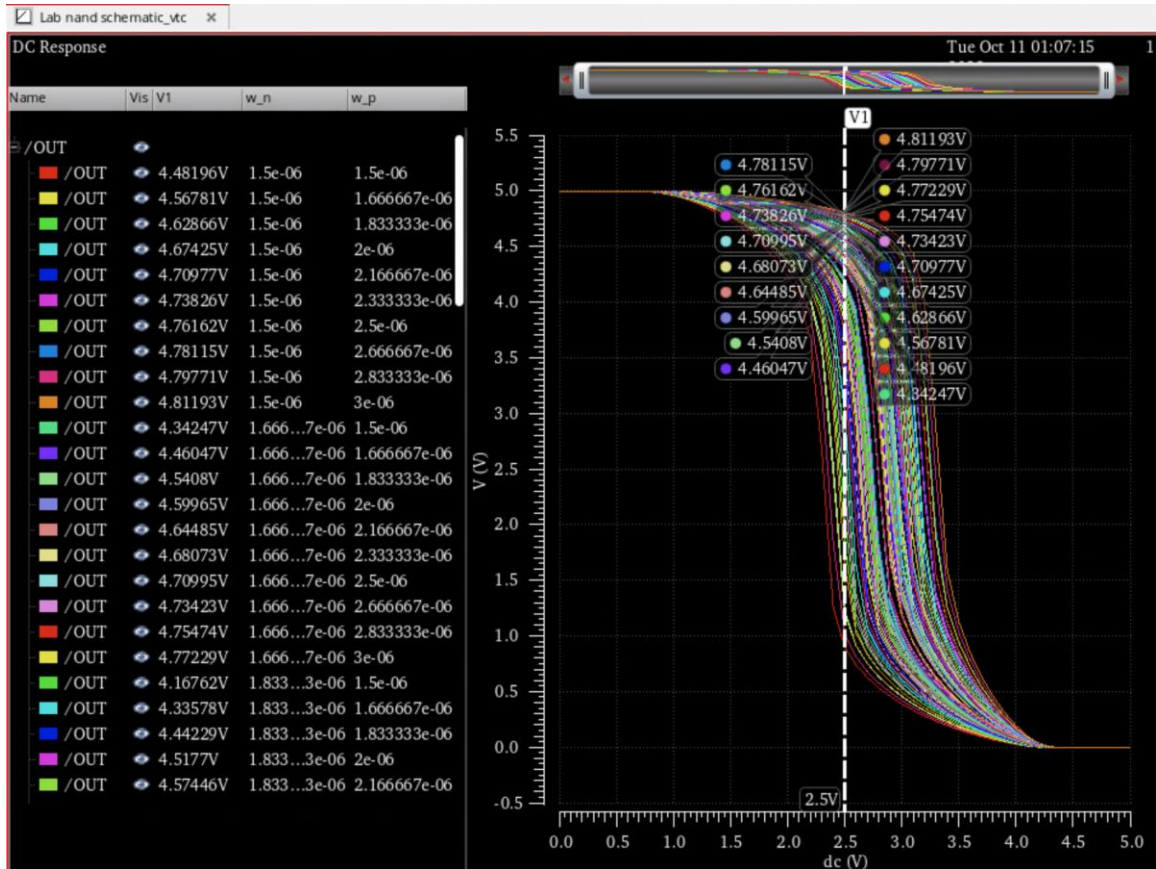


Figure 6 VTC DC Sweep, both transistors varied

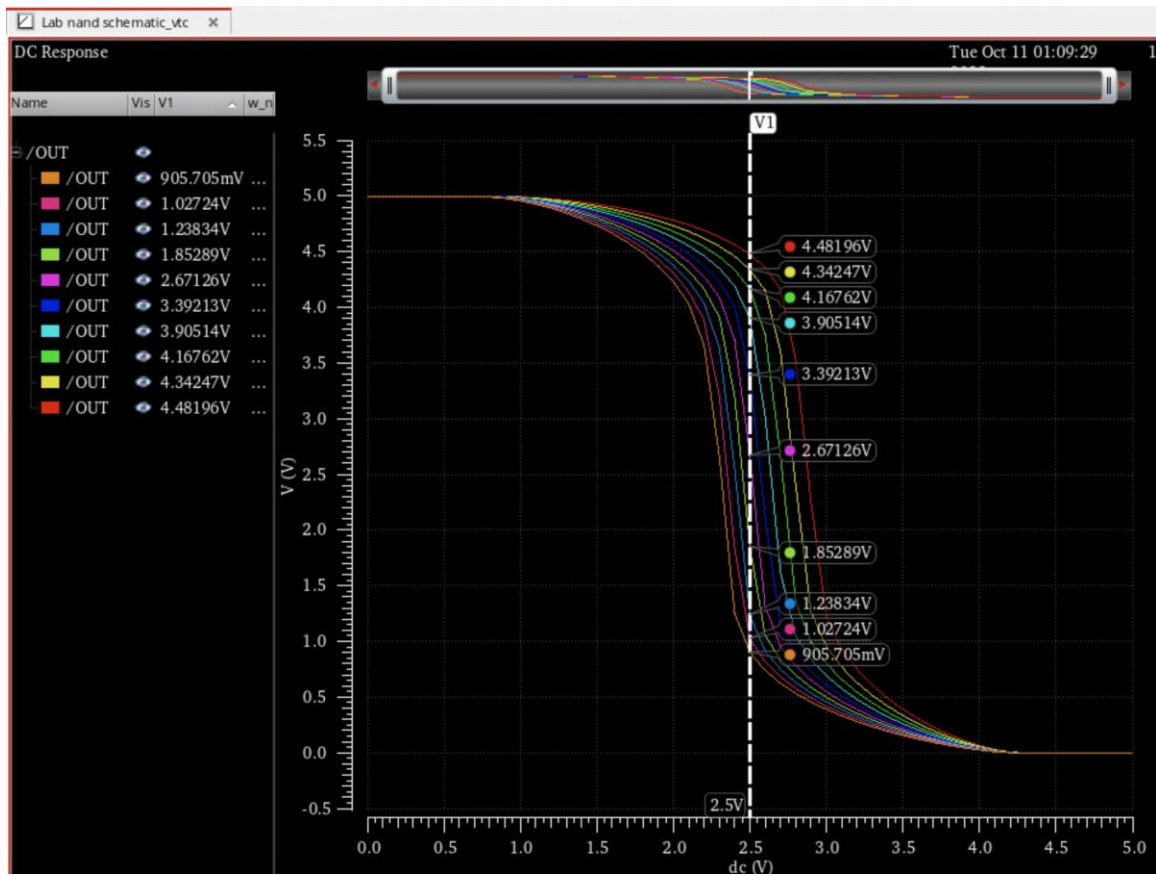


Figure 7 VTC DC Sweep, w_n varied

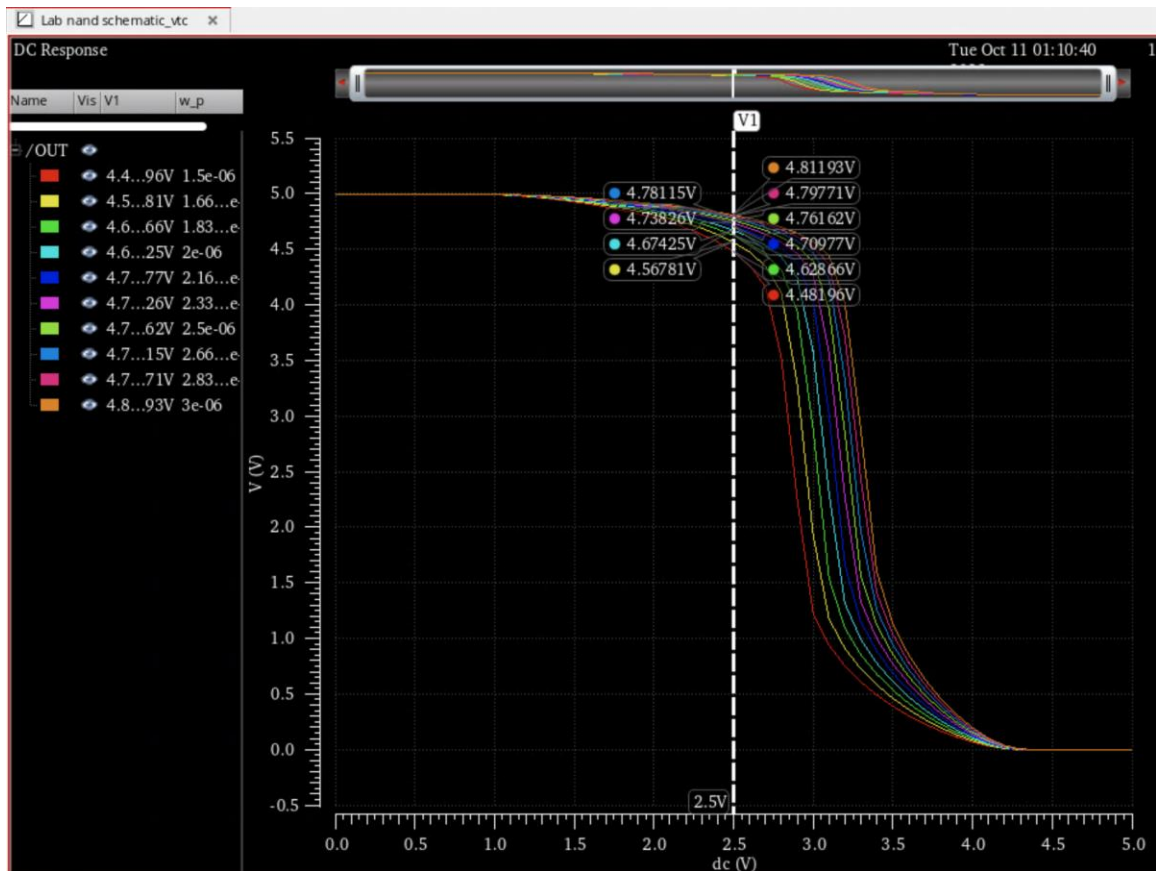


Figure 8 VTC DC Sweep, w_p varied

With $w_p=1.5\mu$ and $w_n=2.3\mu$, we can get 2.5v-2.67v.

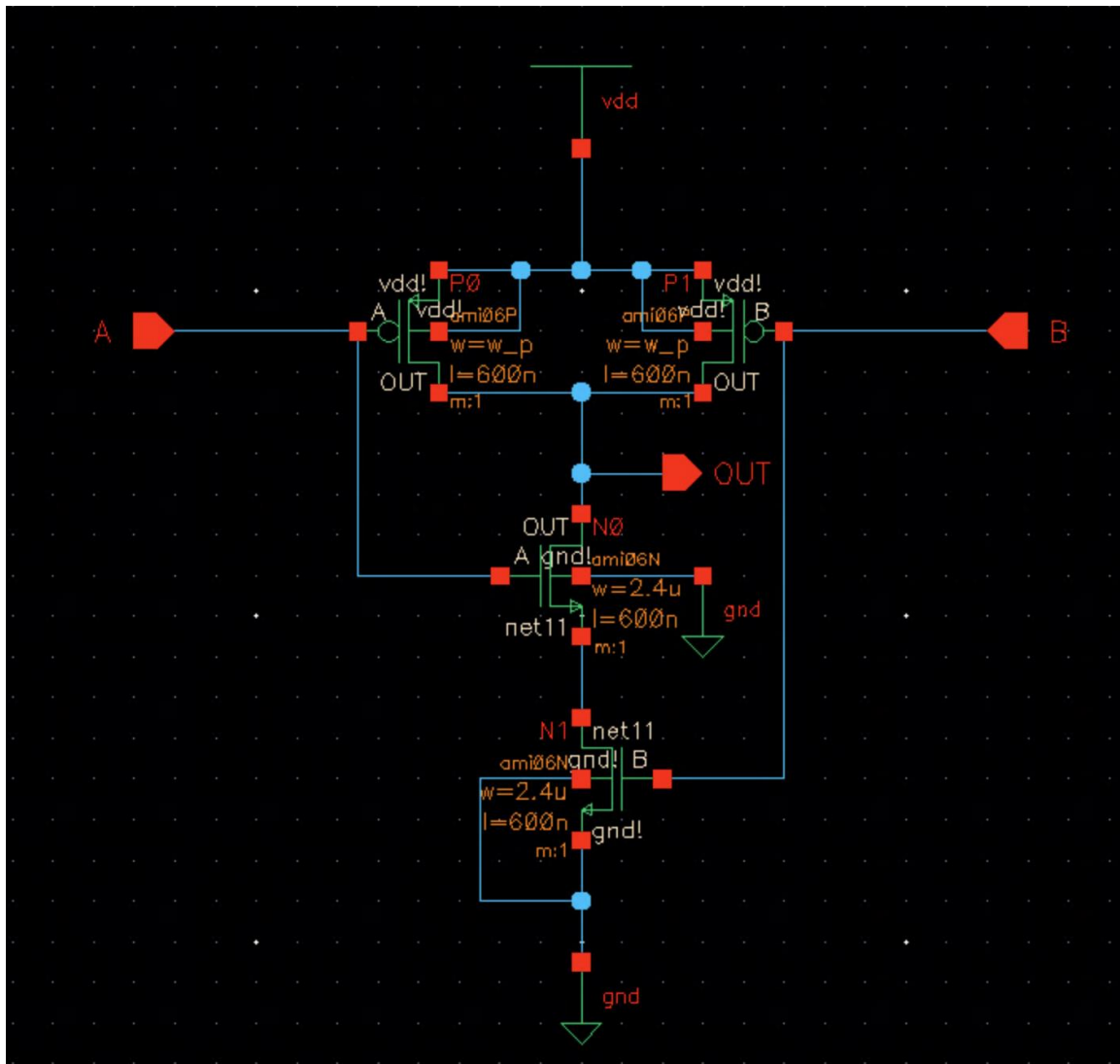


Figure 9 Schematic with new width

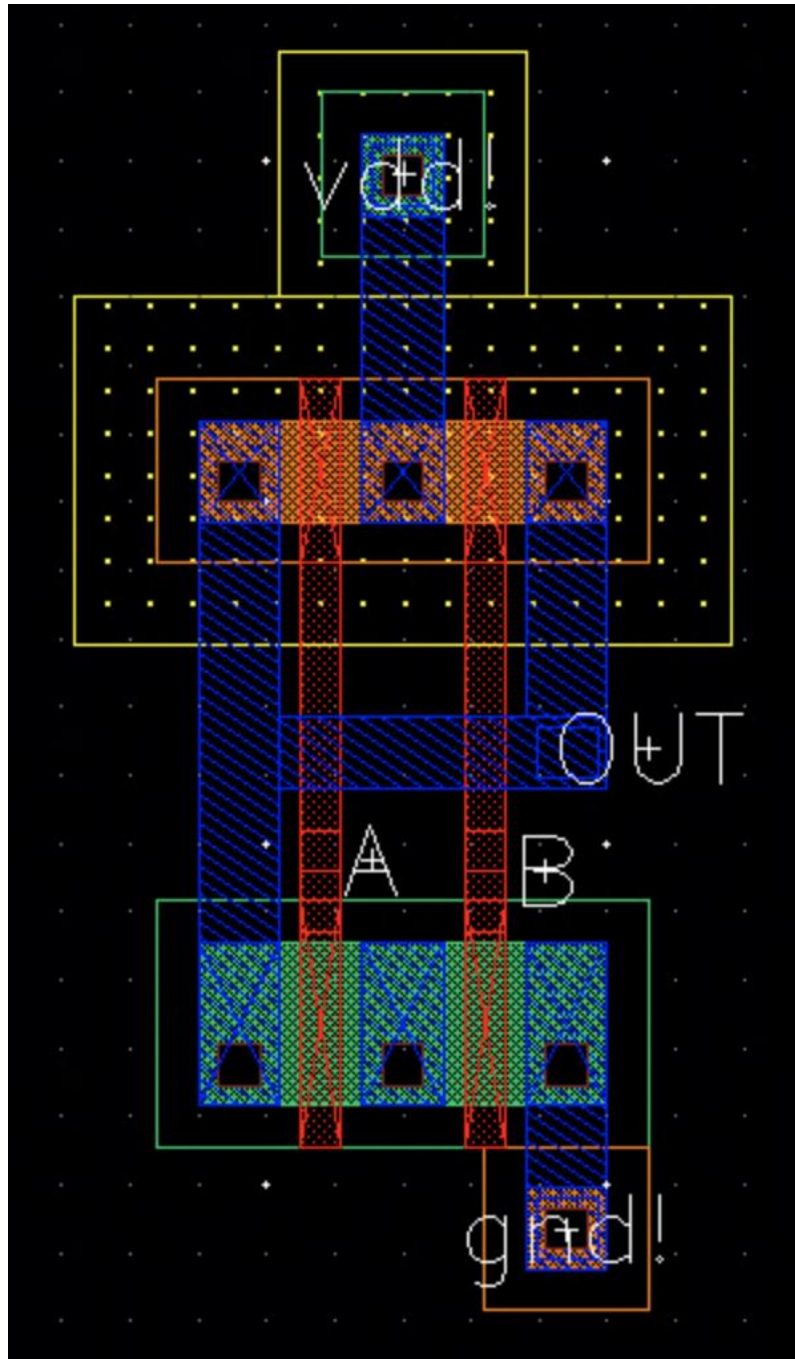


Figure 10 Layout

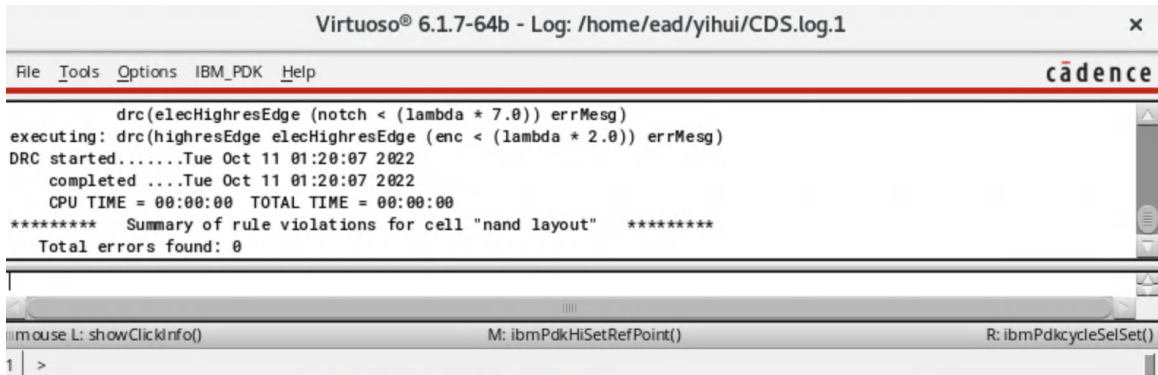


Figure 11 DRC Result

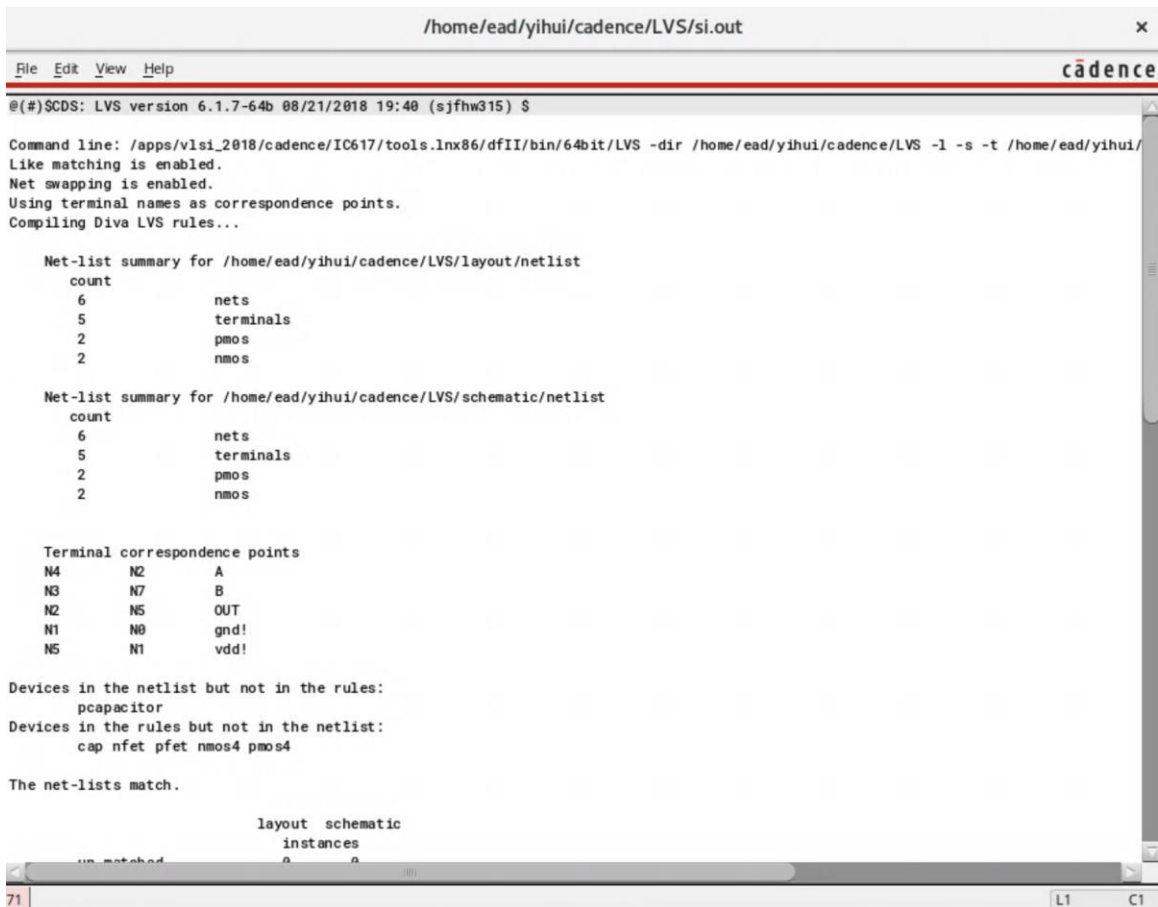


Figure 12 LVS Match

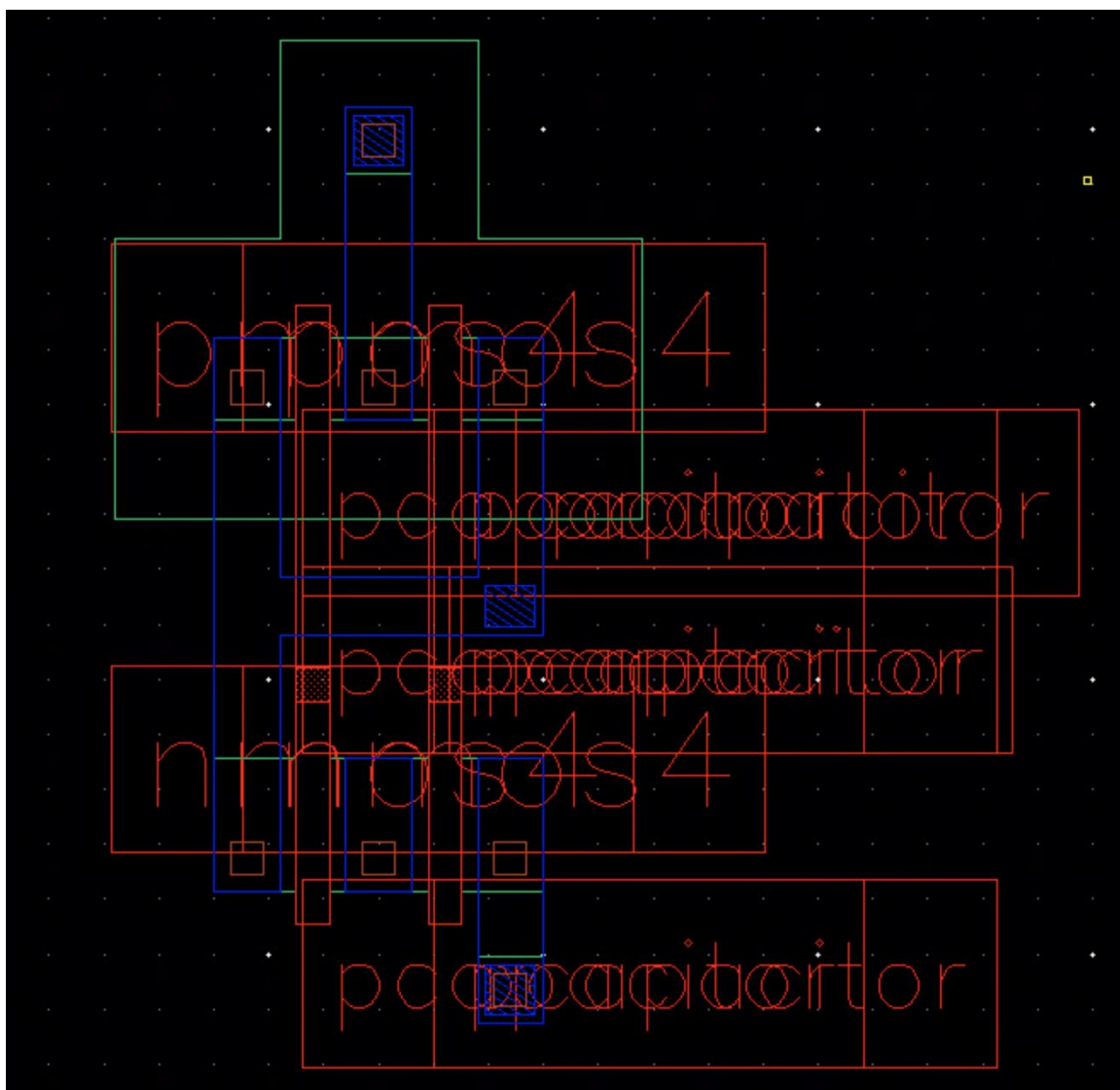


Figure 13 Extracted Layout